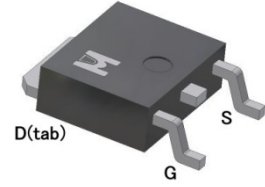
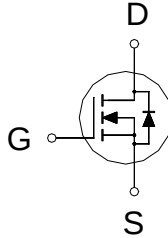


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	20V
$R_{DS(on)} (MAX.)$	13.5m Ω
I_D	48A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	48	A
	$T_C = 100^\circ\text{C}$		20	
Pulsed Drain Current ¹		I_{DM}	140	
Avalanche Current		I_{AS}	33	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	54	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_C = 100^\circ\text{C}$		20	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		2.5	$^\circ\text{C} / \text{W}$
Junction-to-Ambient ³	$R_{\theta JA}$		75	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³75 $^\circ\text{C} / \text{W}$ when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.45	0.75	1.2	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16V, V _{GS} = 0V			1	μA
		V _{DS} = 16V, V _{GS} = 0V, T _J = 125 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 4.5V	48			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 18A		10	13.5	mΩ
		V _{GS} = 2.5V, I _D = 9A		12	20	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 18A		7		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz		1095		pF
Output Capacitance	C _{oss}			185		
Reverse Transfer Capacitance	C _{rss}			164		
Total Gate Charge ^{1,2}	Q _g	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 18A		14.7		nC
Gate-Source Charge ^{1,2}	Q _{gs}			1.9		
Gate-Drain Charge ^{1,2}	Q _{gd}			4.7		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = 10V, I _D = 1A, V _{GS} = 4.5V, R _{GS} = 6Ω		15		nS
Rise Time ^{1,2}	t _r			18		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			35		
Fall Time ^{1,2}	t _f			20		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I _S				22	A
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.3	V
Reverse Recovery Time	t _{rr}			35		nS
Reverse Recovery Charge	Q _{rr}			42		nC

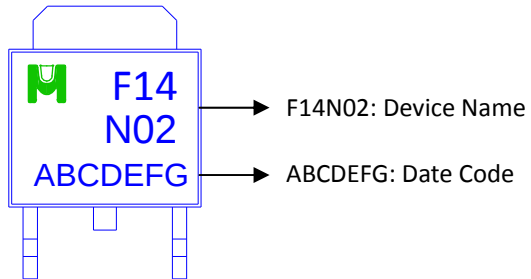
¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

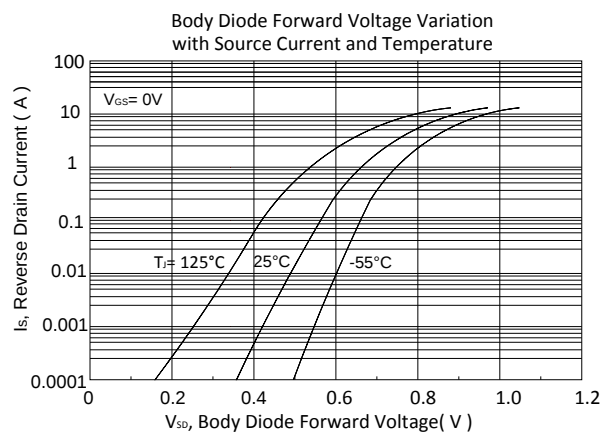
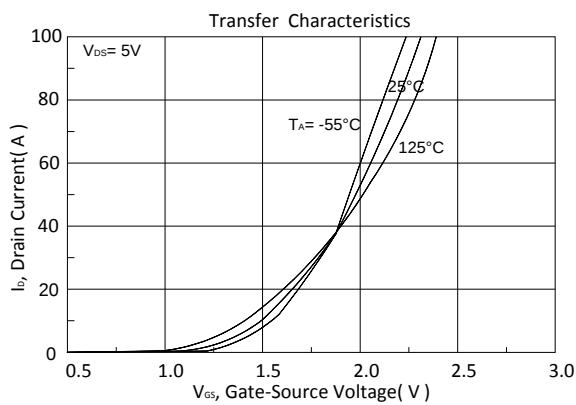
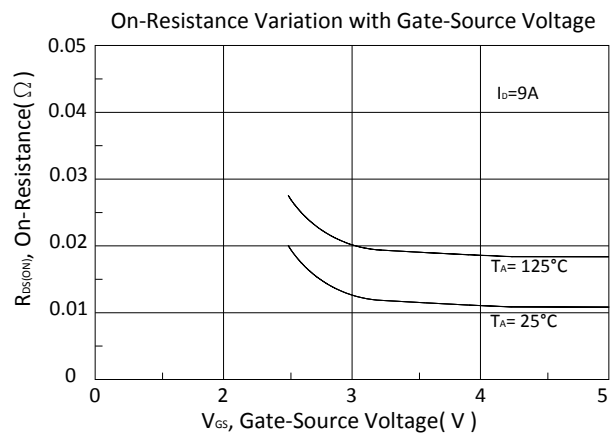
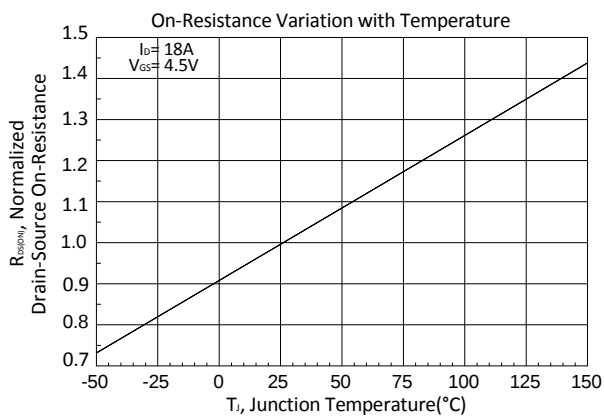
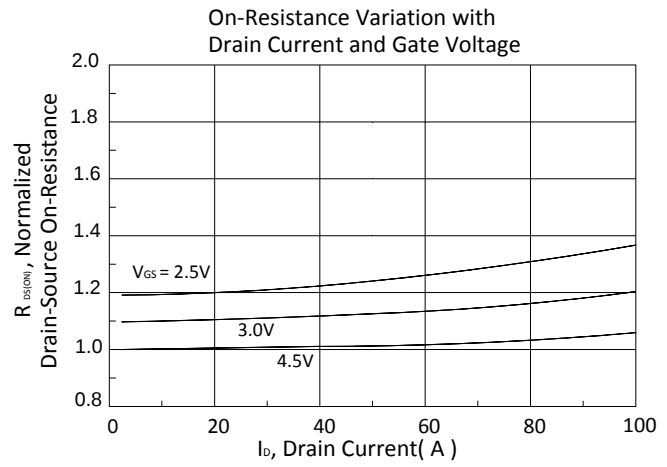
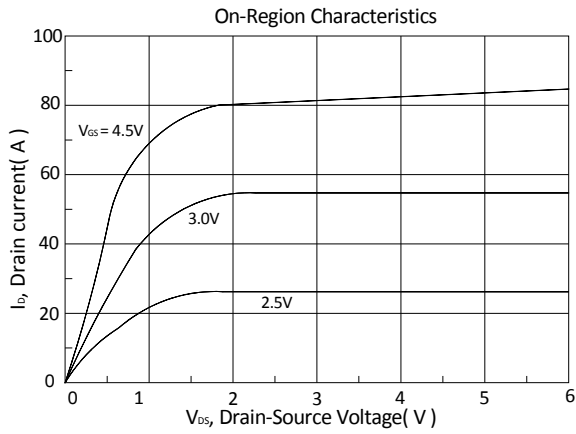
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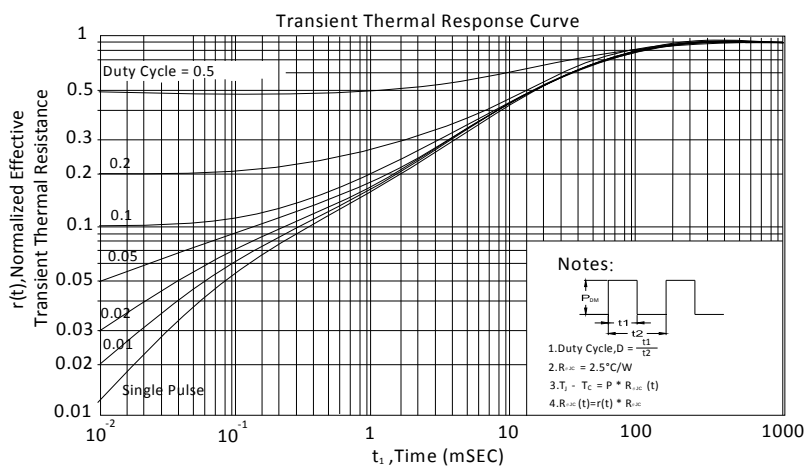
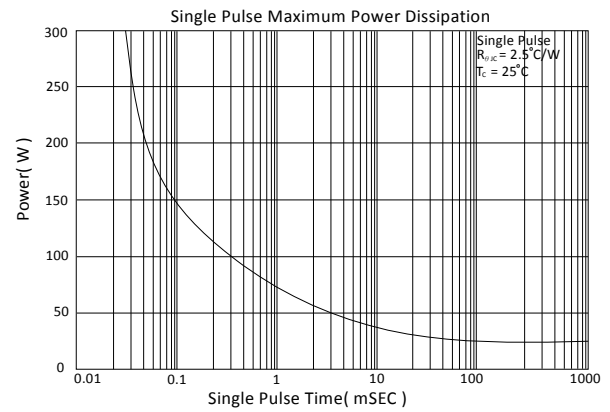
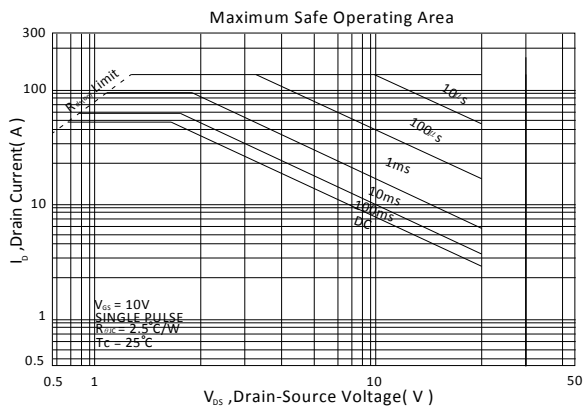
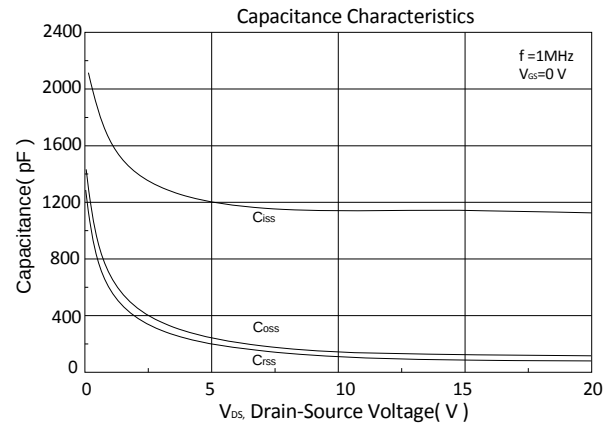
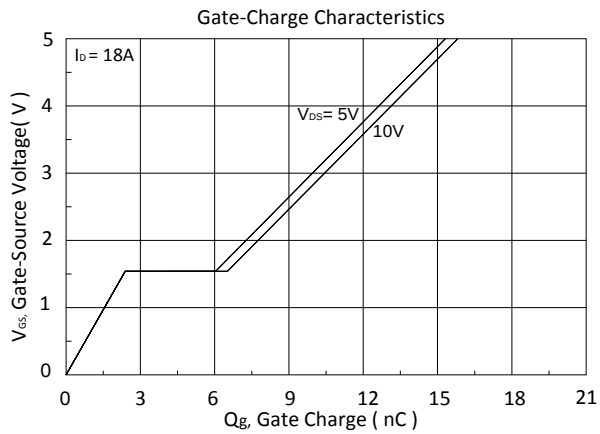
Device Name: EMF14N02A for DPAK (TO-252)



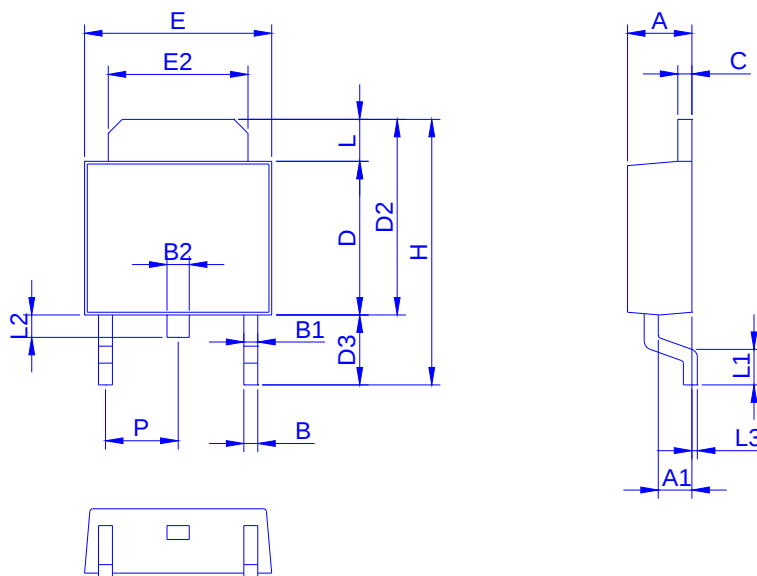


TYPICAL CHARACTERISTICS





Outline Drawing



Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	0.95	0.30	0.40	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10
Max.	2.50	1.30	0.85	0.94	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50

Footprint

